

Mathematical Model of Normal Diode Acting As an Amplifier

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Abstract:- In Our Previous Paper “Diode-Unique Behaviour Documentation In In4007”Published In Ijera (Vol-2,Issue-5,September-October 2012)We Showed Diode Acting As Voltage Amplifier And Voltage Follower With Negligible Loss, Continuing Our Study Int His Paper We Are Giving The Mathematical Model Justifying Our Study

Keywords:- Voltage Amplifier,Unity Follower,Mathmetical Model,Eta = 1 For 0 Vdd And Eta = 100 For Any Non Zero Vdd

I. INTRODUCTION

This is our second paper on the topic , in the first paper “diode-unique behaviour documentation on in4007”published in ijera (vol-2,issue-5,september-october 2012) we have showed practicaly the diode acting as amplifier along with voltage follower with almost no loss, in this paper we are forwarding an absolutely new mathematical model justifying our previous study, we in detail the process of modelling and then we will verify the results. But first lets study the conventional theory. No electrons move through the pn junction at equilibrium. Generally the term bias refers to the use of a dc voltage to establish certain operating conditions for an electronic device. In relation to a diode, there are two bias conditions: forward and reverse biasing. Either of these bias conditions is established by connecting a sufficient dc voltage of the proper polarity across the pn junction.

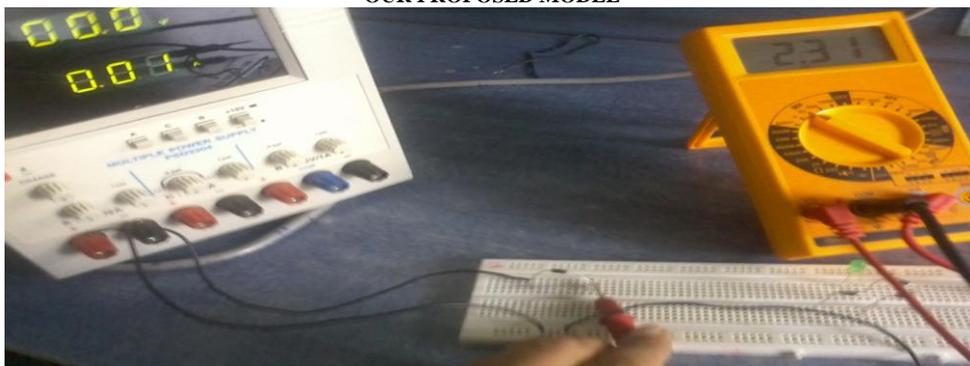
Forward Biasing:

To bias a diode, we apply dc voltage across it. Forward bias is the condition that allows current through the pn junction as shown in below figure, a dc voltage source connected by conductive material (contacts and wire) across a diode in the direction to get forward bias. This external bias voltage is designated as V (Bias). The resistor, R, limits the current to a value that will not damage the diode. The negative side of V Bias is connected to the n region of the diode and the positive side to the p region . This is one requirement for forward bias. A second requirement is that the bias voltage, V_{Bias} , must be greater than the barrier potential

Reverse Biasing:

Reverse Biasing is the condition that essentially prevents current through the diode, as we can see below in figure that a dc voltage source connected across a diode in the direction to produce reverse biasing. This external Bias voltage is designated as V BIAS just as it was for forward bias. Notice that the positive side of V BIAS is connected to the n region of the diode and the negative side is connected to the p region. Also note that the depletion region is shown much wider than in forward bias or equilibrium.

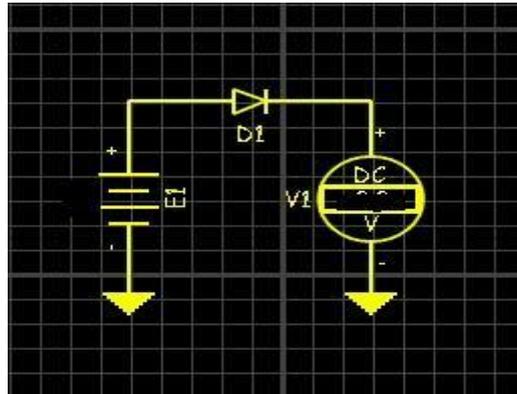
OUR PROPOSED MODEL





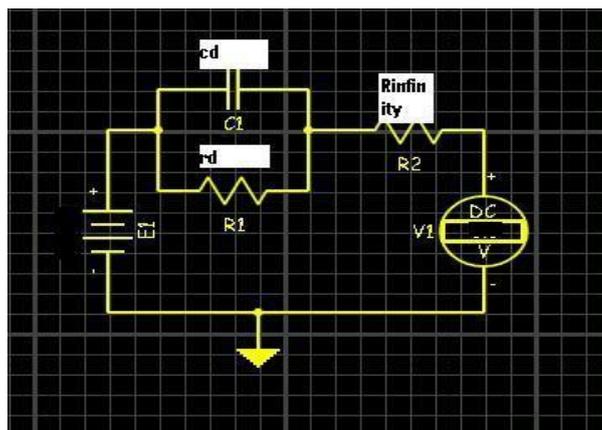
DEDUCTION OF THE MODEL

The circuit connection for diode in above behavior is



Experimental set-up

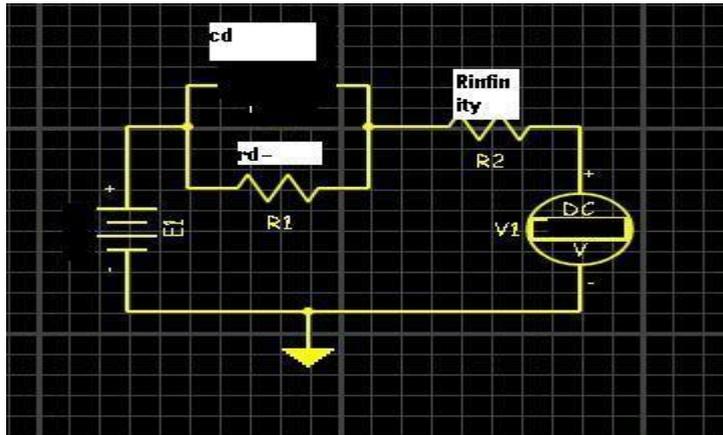
The above diagram illustrates diode in with supply voltage and voltmeter connected between cathode and ground of diode.



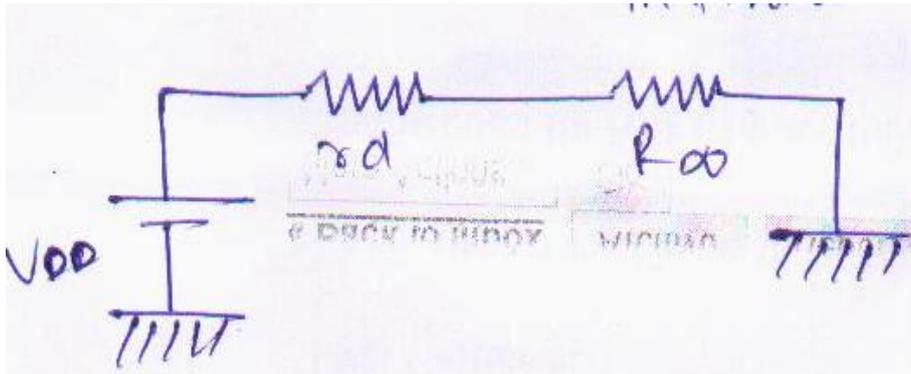
1st deduced step

In the above step we are replacing the diode with internal resistance r_d and capacitance c_d . the voltmeter is having infinite internal resistance thus replacing it with R_∞ .

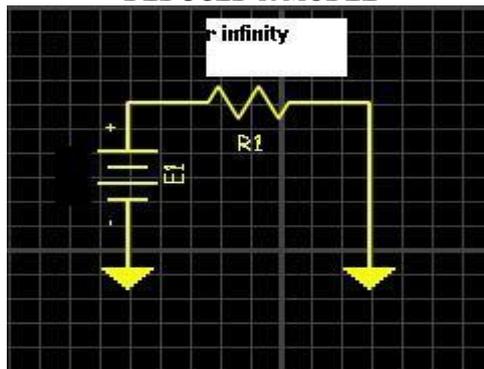
R model deduction



2ND DEDUCED STEP



DEDUCED R MODEL



Final deduced model

In the first step we open circuited the internal capacitor as we are using d.c input the capacitor has no role to play. No it comes internal diode resistance r_d in series with r_∞ . as per the principle there remains only one effective resistance and that is r_∞

II. MATHEMATICAL ANALYSIS OF ABOVE DEDUCED MODEL

Normal diode equation is $V_{DD} = V_D + I R_\infty$ now $I = I_S (e^{\frac{V_D}{\eta V_T}} - 1)$

$$V_D = V_{DD} - (I_S (e^{\frac{V_D}{\eta V_T}} - 1) R_\infty)$$

$V_D = V_{DD} - I_S e^{\frac{V_D}{\eta V_T}} R_\infty + I_S \times R_\infty$ (basic understanding says higher will be the resistance lower will be the current keeping in mind this diode not showing negative resistance propert)

$V_D = V_{DD} - \infty + \infty$ (mathematical convention any operations with infinity yields the result infinity)

$V_D = \infty$. I solved the above equation conceptually yielding diode outp put voltage infinity. Which definitely don't stand true.

So now trying to deduce the above equation in mathematical pure way

$$V_D = V_{DD} - I_S \times R_\infty (e^{\frac{V_D}{\eta V_T}} - 1)$$

$$V_D = V_{DD} - e^{\frac{V_D}{\eta V_T}} + 1 \quad (IS \times R_{\infty} \text{ is ineffective since infinite resistance will give effective zero current})$$

III. FINAL MATHEMATICAL EQUATION

$V_D = V_{DD} - e^{\frac{V_D}{\eta V_T}} + 1$ ($\eta = 1$ for $v_{dd} = 0$ and $\eta = 100$ for $v_{dd} \gg 0$) (we are replacing V_T with v_{ak} voltage observed across anode and cathode. We are doing this as to inculcate diode behavior in terms of all apparent quantities. In all previous study they did not considered all apparent parameter instead they included variable factor thermal voltage, and this started a new trend of incomplete documentation)

PRACTICAL READINGS AND VERIFICATION

VA/VDD (SUPPLY VOLTAGE AT ANODE)	VAK(VOLTAGE BETWEEN ANODE AND CATHODE)	VK/VD (VOLTAGE OBTAINED AT CATHODE, I.E BETWEEN CATHODE AND GROUND)	MATHEMATICAL VOLTAGE AFTER CALCULATION	ERROR BETWEEN PRACTICAL RESULT AND CALCULATED RESULT
0v	1.51V	1.51v	1.71v	0.2v
5v	1.71V	5.06v	4.99v	0.07v
10v	1.82V	9.86v	9.95	0.09v
15v	1.70V	14.87v	14.92	0.05v
20v	1.52V	19.83v	19.87	0.04v
25v	1.9V	24.8v	24.81	0.01v
30v	1.6V	29.8v	29.81	0.01v

When $v_{dd} = 0v$ and $v_k = 1.51V$ and $v_{ak} = 1.51v$

$$V_d = 0 - e^{\frac{1.51}{1 \times 1.51}} + 1$$

$$V_d = 1 - 2.71$$

$$V_d = 1.71v$$

When $v_{dd} = 5v$ and $v_k = 5.06V$ and $v_{ak} = 1.71v$

$$V_d = 5 - e^{\frac{5.06}{100 \times 5.06}} + 1$$

$$V_d = 6 - 1.01v$$

$$V_d = 4.99v$$

When $v_{dd} = 10v$ and $v_k = 9.86V$ and $v_{ak} = 1.82v$

$$V_d = 10 - e^{\frac{9.86}{100 \times 1.82}} + 1$$

$$V_d = 11 - 1.05v$$

$$V_d = 9.95v$$

When $v_{dd} = 15v$ and $v_k = 14.87V$ and $v_{ak} = 1.70v$

$$V_d = 15 - e^{\frac{14.87}{100 \times 1.70}} + 1$$

$$V_d = 16 - 1.08v$$

$$V_d = 14.92v$$

When $v_{dd} = 20v$ and $v_k = 19.83V$ and $v_{ak} = 1.52v$

$$V_d = 20 - e^{\frac{19.83}{100 \times 1.52}} + 1$$

$$V_d = 21 - 1.13v$$

$$V_d = 19.87v$$

When $v_{dd} = 30v$ and $v_k = 29.8V$ and $v_{ak} = 1.6v$

$$V_d = 30 - e^{\frac{29.8}{100 \times 1.6}} + 1$$

$$V_d = 31 - 1.19v$$

$$V_d = 29.81v$$

VA/VDD (SUPPLY VOLTAGE AT ANODE)	VAK(VOLTAGE BETWEEN ANODE AND CATHODE)	VK/VD (VOLTAGE OBTAINED AT CATHODE, I.E BETWEEN CATHODE AND GROUND)	MATHEMATICAL VOLTAGE AFTER CALCULATION	ERROR BETWEEN PRACTICAL RESULT AND CALCULATED RESULT
0v	1.64V	2v	2.35v	0.35v

5v	1.93V	5.06v	4.91v	0.15v
10v	1.39V	9.85v	9.93v	0.08v
15v	1.40V	14.91v	14.9v	0.01v
20v	1.14V	19.90v	19.87v	0.03v
25v	1.2V	24.9v	24.78v	0.03v
30v	0.9V	29.9v	30.67v	0.7v

When vdd = 0v and vk = 2V and vak = 1.64v

$$Vd = 0 - e_{1 \times 1.64}^2 + 1$$

$$Vd = 1 - 3.35$$

$$Vd = 2.35v$$

When vdd = 5v and vk = 5.06V and vak = 1.93v

$$Vd = 5 - e_{100 \times 1.93}^{5.06} + 1$$

$$Vd = 6 - 1.09v$$

$$Vd = 4.91v$$

When vdd = 10v and vk = 9.85V and vak = 1.39v

$$Vd = 10 - e_{100 \times 1.39}^{9.85} + 1$$

$$Vd = 11 - 1.07v$$

$$Vd = 9.93v$$

When vdd = 15v and vk = 14.91V and vak = 1.40v

$$Vd = 15 - e_{100 \times 1.40}^{14.91} + 1$$

$$Vd = 16 - 1.10v$$

$$Vd = 14.9v$$

When vdd = 25v and vk = 24.9V and vak = 1.2v

$$Vd = 25 - e_{100 \times 1.2}^{24.9} + 1$$

$$Vd = 26 - 1.22v$$

$$Vd = 24.78v$$

When vdd = 30v and vk = 29.9V and vak = 0.9v

$$Vd = 30 - e_{100 \times 0.9}^{29.9} + 1$$

$$Vd = 31 - 1.07v$$

$$Vd = 30.67v$$

IV. CONCLUSIONS

thus we conclude the documentation of amplification/unity follower behaviour of IN4007 diode.this is the unique documentation of its type in the world so we take pleasure in naming this model as “mobassir niyaz diode amplification model”.

REFERENCES

- 1) Imtaiyazul haque, haque mobassir imtiyaz, niyaz ahmed abdul mateen khan & veena narayankar “diode:- unique behavior documentation on in4007 diode, ijera vol-2 issue-5,sept-oct 2012,pp 861-864”

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